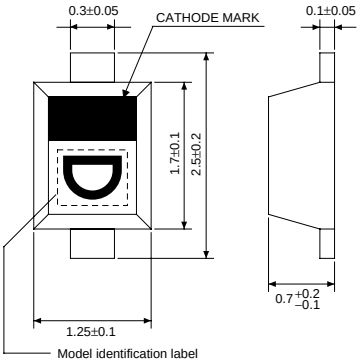
Switching diode

1SS376

●**Applications**
High voltage switching

●**Features**
1) Small surface mounting type. (UMD2)
2) V_{RM}=300V guaranteed.
3) High reliability.

●**Construction**
Silicon epitaxial planar



ROHM : UMD2
EIAJ : SC-76
JEDEC : SOD-323

●**External dimensions** (Units : mm)

●**Absolute maximum ratings** (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	300	V
DC reverse voltage	V_R	250	V
Peak forward current	I_{FM}	300	mA
Mean rectifying current	I_O	100	mA
Surge current (10ms)	I_{surge}	2	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−55~+125	°C

●**Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditons
Forward voltage	V_F	–	–	1.2	V	I_F=100mA
Reverse current	I_R	–	–	0.2	μA	V_R=250V
Reverse current	I_R	–	–	100	μA	V_R=300V
Capacitance between terminals	C_T	–	–	3	pF	V_R=0V, f=1MHz
Reverse recovery time	trr	–	–	100	ns	I_R=30mA, I_F=30mA, Irr=3mA

●**Electrical characteristic curves** (Ta = 25°C)

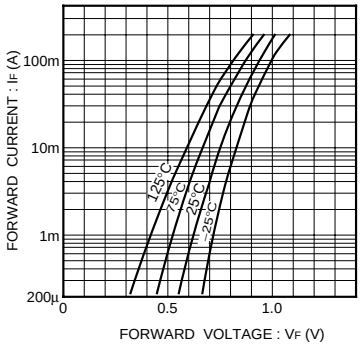


Fig.1 Forward characteristics

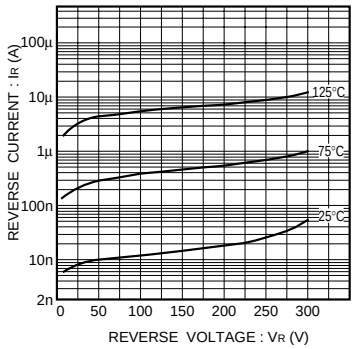


Fig.2 Reverse characteristics

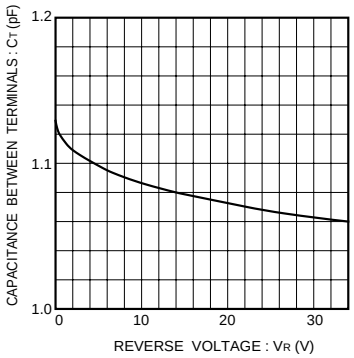


Fig.3 Capacitance between terminals characteristics

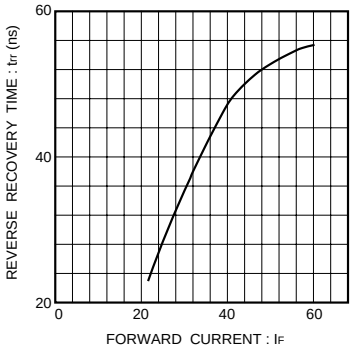


Fig.4 Reverse recovery time characteristics

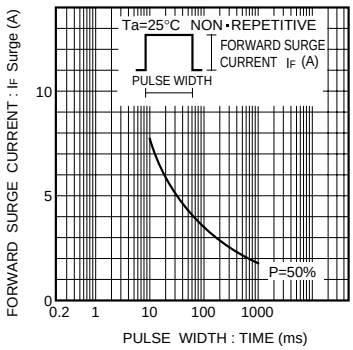


Fig.5 Surge current characteristics

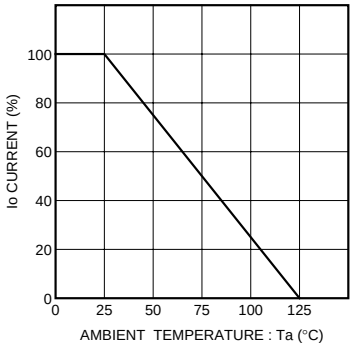


Fig.6 Derating curve (mounting on glass epoxy PCBs)